

[查询"2SC5850"供应商](#)

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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2SC5850

Silicon NPN Epitaxial

RENESAS

ADE-208-1479 (Z)

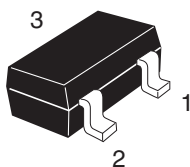
Rev.0
Feb. 2002

Features

- Low frequency amplifier

Outline

CMPAK



1. Emitter
2. Base
3. Collector

2SC5850

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	50	V
Collector to emitter voltage	V_{CEO}	40	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Emitter current	I_E	-100	mA
Collector power dissipation	P_C^*	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +125	°C

*Value on the glass epoxy board (10 mm x 10 mm x 0.7 mm)

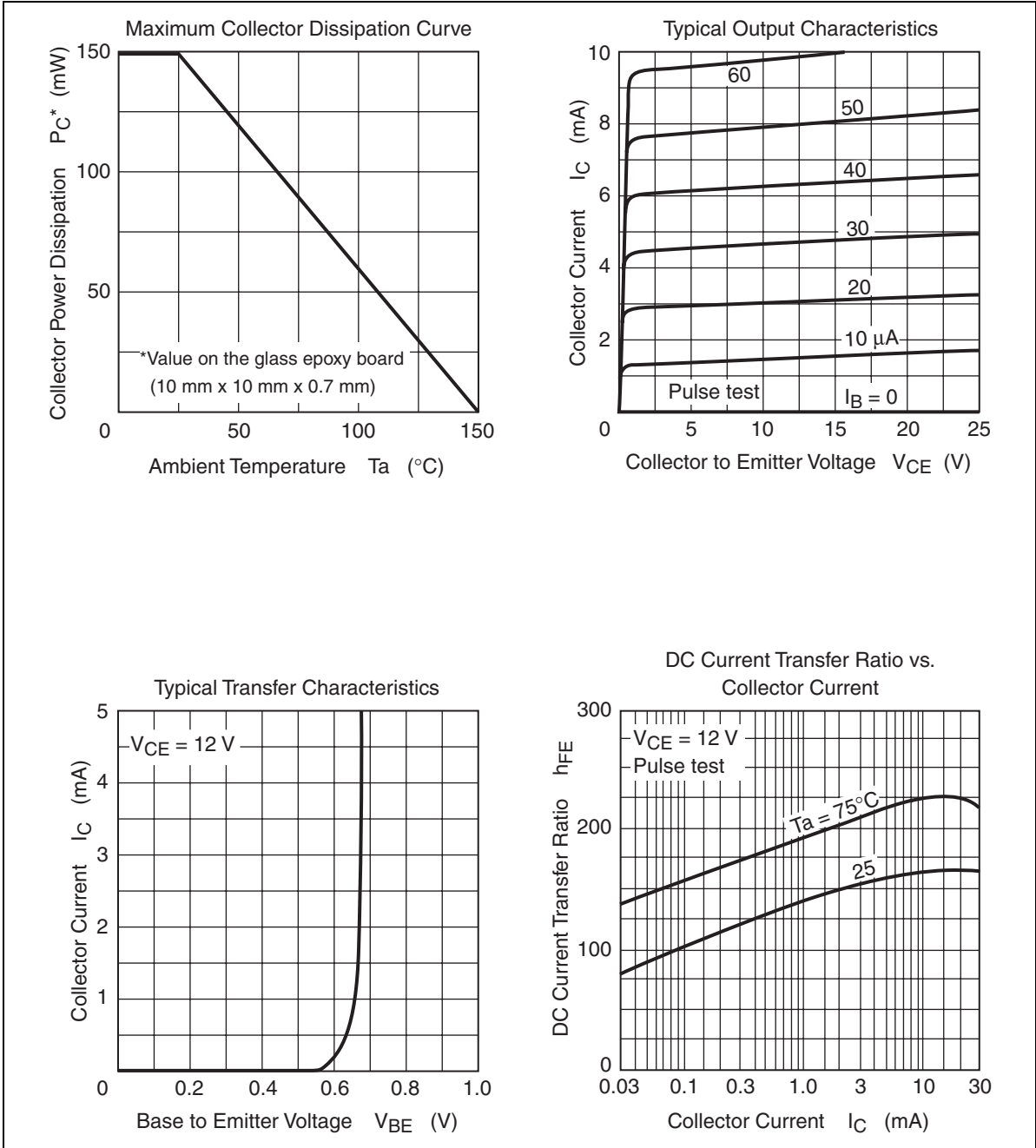
Electrical Characteristics

(Ta = 25°C)

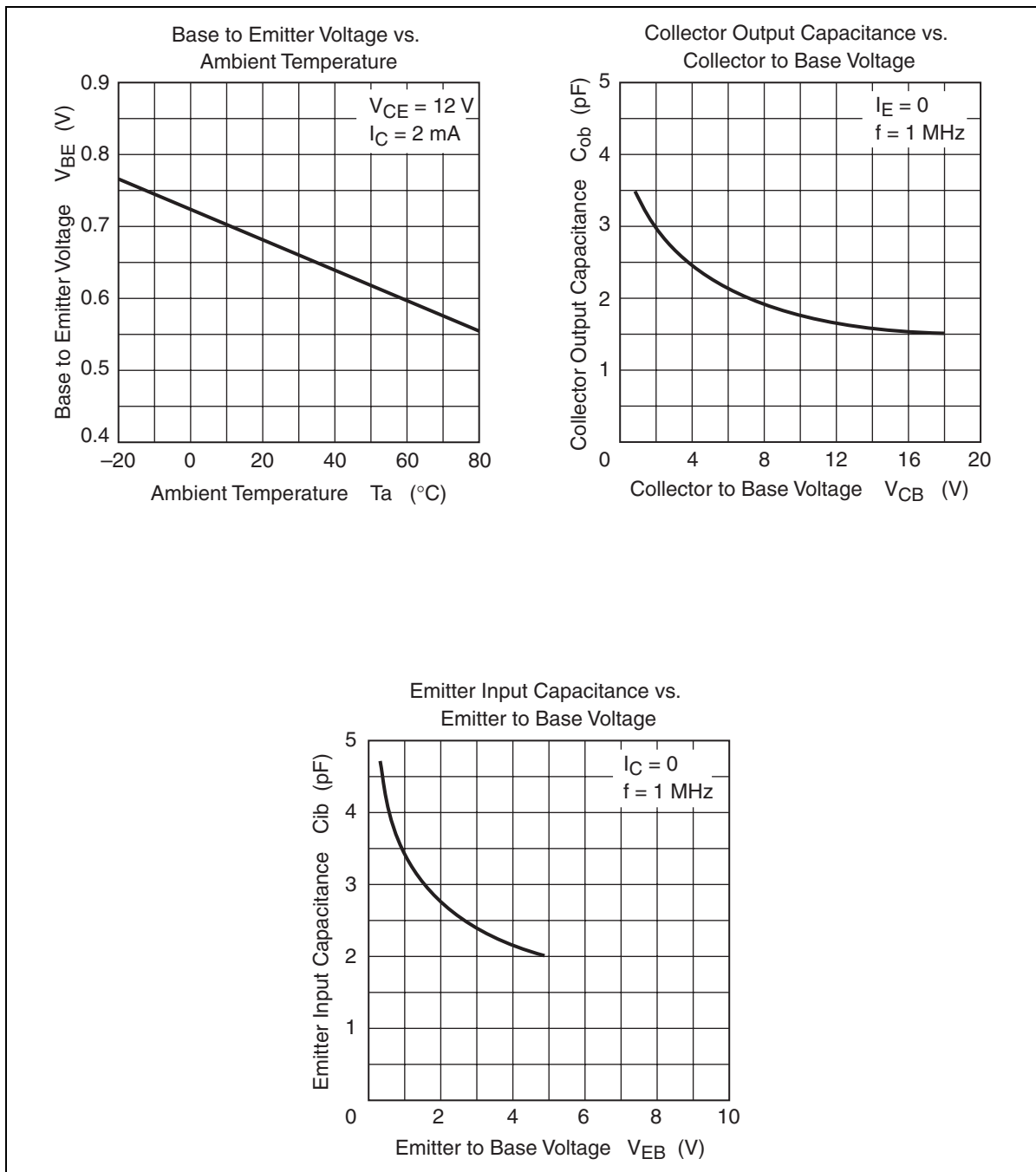
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	40	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 30 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	500	—	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$

Notes: 1. The 2SC5850 is grouped by h_{FE} as follows.

Grade	B	C	D
Mark	LB	LC	LD
h_{FE}	100 to 200	160 to 320	250 to 500

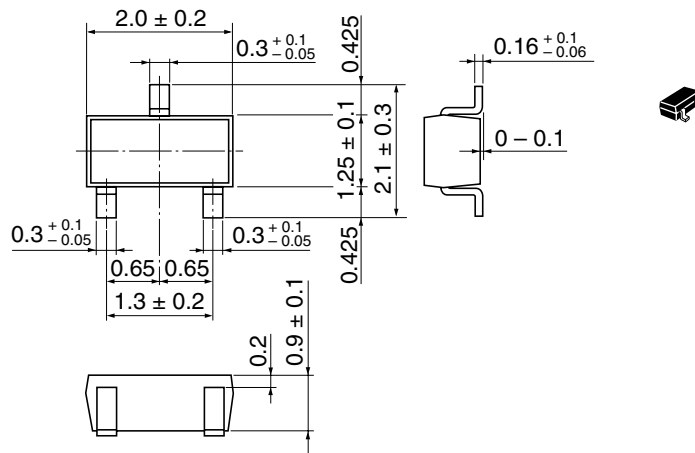


2SC5850



Package Dimensions

As of July, 2001
Unit: mm



Hitachi Code	CMPAK
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.006 g

2SC5850

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